

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A plasma generating electrode comprising at least two opposing plate-shaped unit electrodes, each having a rectangular surface and four end faces, and a holding member which holds a fixed end of a first pair of parallel end faces of the unit electrode in a state in which the unit electrodes are separated at a specific interval, and is capable of generating plasma upon application of voltage between the unit electrodes,

at least one of the opposing unit electrodes being a conductive-film-containing electrode including a ceramic body as a dielectric and a conductive film disposed inside the ceramic body, and

a distance “a” from an edge of the conductive film to an edge of the ceramic body on a second pair of parallel end faces of the conductive-film-containing electrode adjacent to the first pair of parallel end faces and a thickness “c” of the ceramic body satisfying a relationship $\frac{c}{2} \leq a \leq 5c$ and $\frac{c}{2} \leq a \leq 2c$.

2. (Previously Presented) The plasma generating electrode according to claim 1, wherein a distance “b” from the edge of the conductive film to the edge of the ceramic body on the fixed end of the conductive-film-containing electrode and the thickness “c” of the ceramic body satisfy a relationship $2c \leq b \leq 10c$.

3. (Previously Presented) The plasma generating electrode according to claim 1, wherein, when the first pair of parallel end faces of the conductive-film-containing electrode has a free end opposite to the fixed end, a distance “d” from the edge of the conductive film to the edge of the ceramic body on the free end and the thickness “c” of the ceramic body satisfy a relationship $\frac{c}{2} \leq d \leq 5c$.

4. (Previously Presented) The plasma generating electrode according to claim 1, wherein the conductive film has a thickness of 5 to 30 μm .
5. (Previously Presented) The plasma generating electrode according to claim 1, wherein the ceramic body includes at least one ceramic selected from the group consisting of alumina, mullite, ceramic glass, zirconia, cordierite, silicon nitride, aluminum nitride, and glass.
6. (Previously Presented) The plasma generating electrode according to claim 1, wherein the conductive film includes at least one metal selected from the group consisting of tungsten, molybdenum, manganese, chromium, titanium, zirconium, nickel, iron, silver, copper, platinum, and palladium.
7. (Previously Presented) A plasma reactor comprising:
the plasma generating electrode according to claim 1; and
a casing having a gas passage, wherein, when a gas is introduced into the gas passage of the casing, a specific component contained in the gas can be reacted using plasma generated by the plasma generating electrode.
8. (Previously Presented) The plasma reactor according to claim 7, further comprising a pulsed power supply for applying voltage to the plasma generating electrode.
9. (Original) The plasma reactor according to claim 8, wherein the pulsed power supply includes at least one SI thyristor.
10. (Previously Presented) The plasma generating electrode according to claim 1, wherein the ceramic body is a dense ceramic and the ceramic body and the conductive film are integrated.
11. (New) The plasma generating electrode according to claim 1, wherein the thickness "c" of the ceramic body is less than .38mm.

12. (New) The plasma generating electrode according to claim 1, wherein the thickness "c" of the ceramic body is .25mm or less.

13. (New) The plasma generating electrode according to claim 1, wherein the thickness "c" of the ceramic body is greater than 1mm.